Journal name

ARTICLE

Supporting Material for

Adjust the band structure and defects of ZnO quantum dots via tin doping

Received 00th January 20xx,
Accepted 00th January 20xx

DOI: 10.1039/x0xx00000x

www.rsc.org/

This PDF file includes:

Figs. s1 to s6

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DOI: 10.1039/x0xx00000x

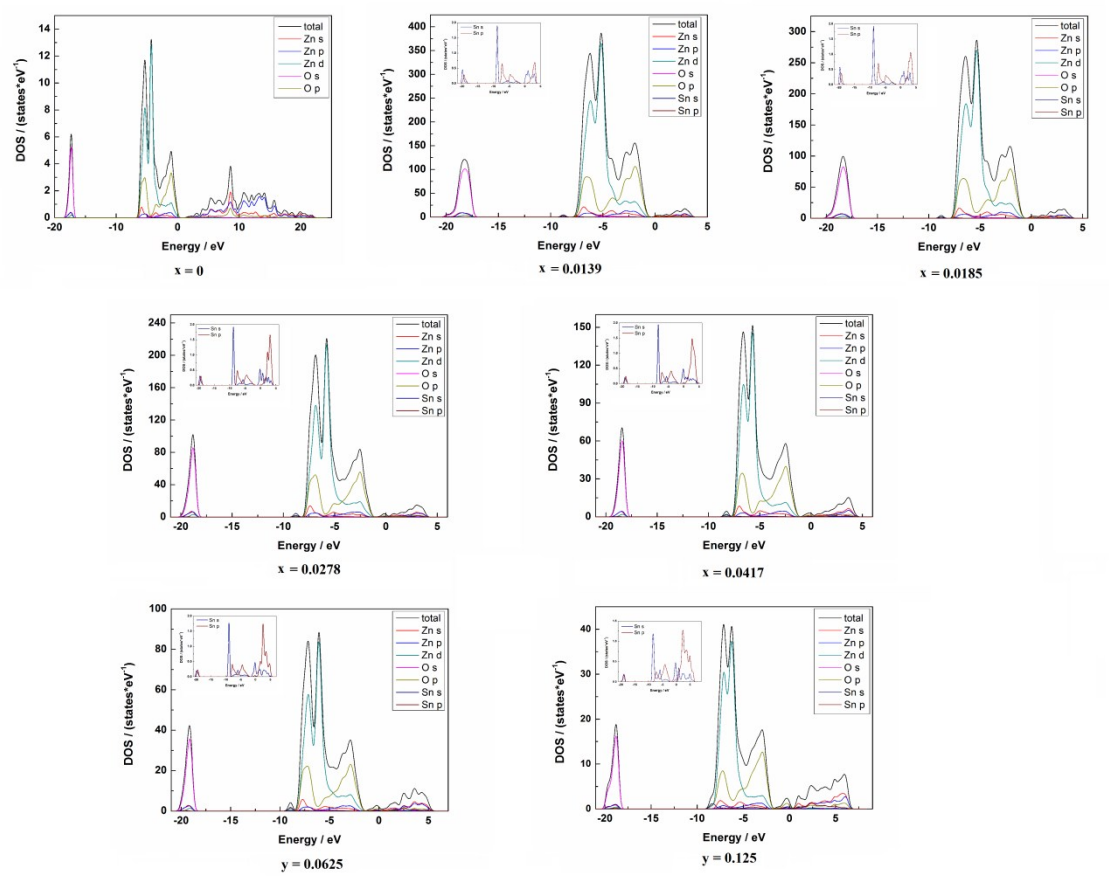

Figure s1 Calculated total DOS and partial DOS of $Zn_{1-X}Sn_xO$. (Small Figures on the upper left are PDOS of Sn^{2+})

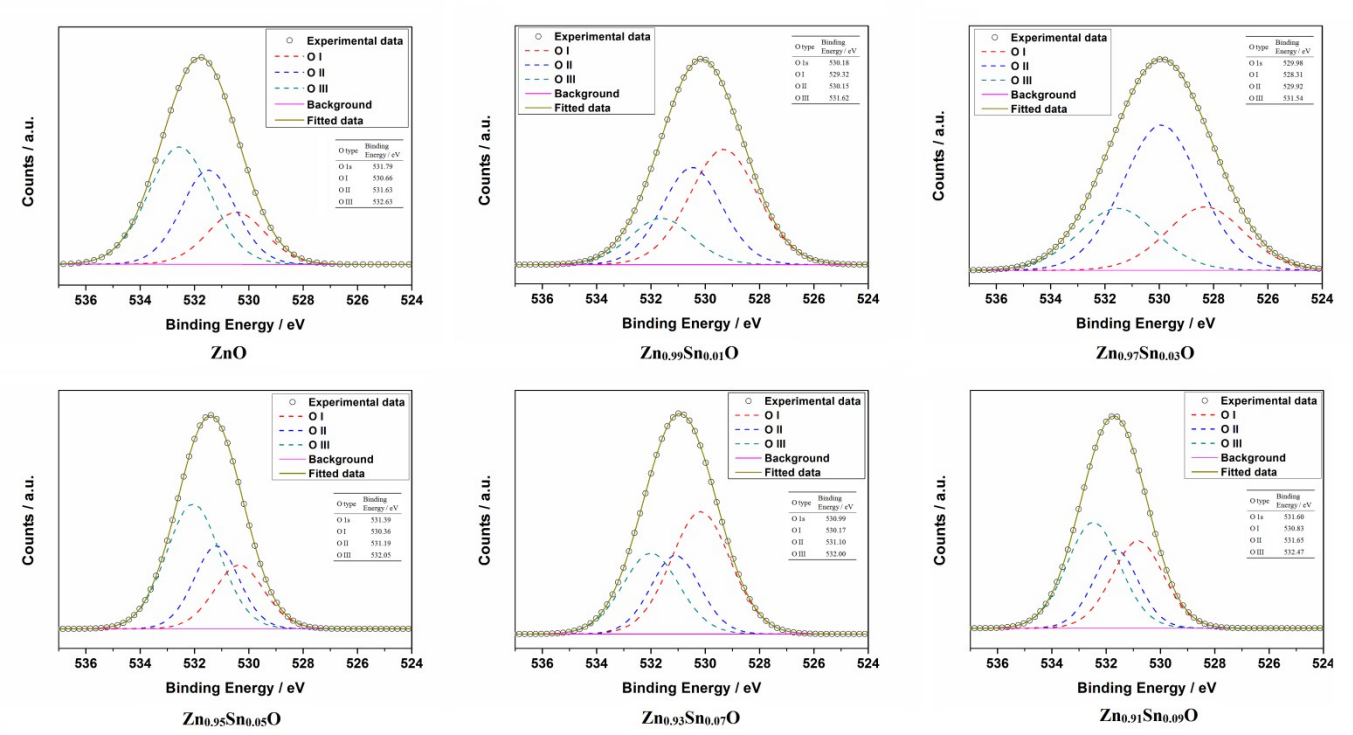

Figure s2 O 1s XPS spectra of $Zn_{1-x}Sn_xO$ QDs synthesized in 40 °C with 180 W ultrasonic power for 30 min.

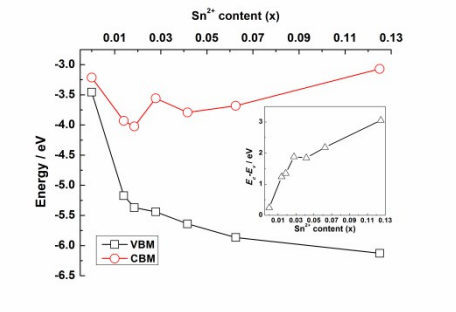

Figure s3 Orbital properties of Sn^{2+} doping ZnO.

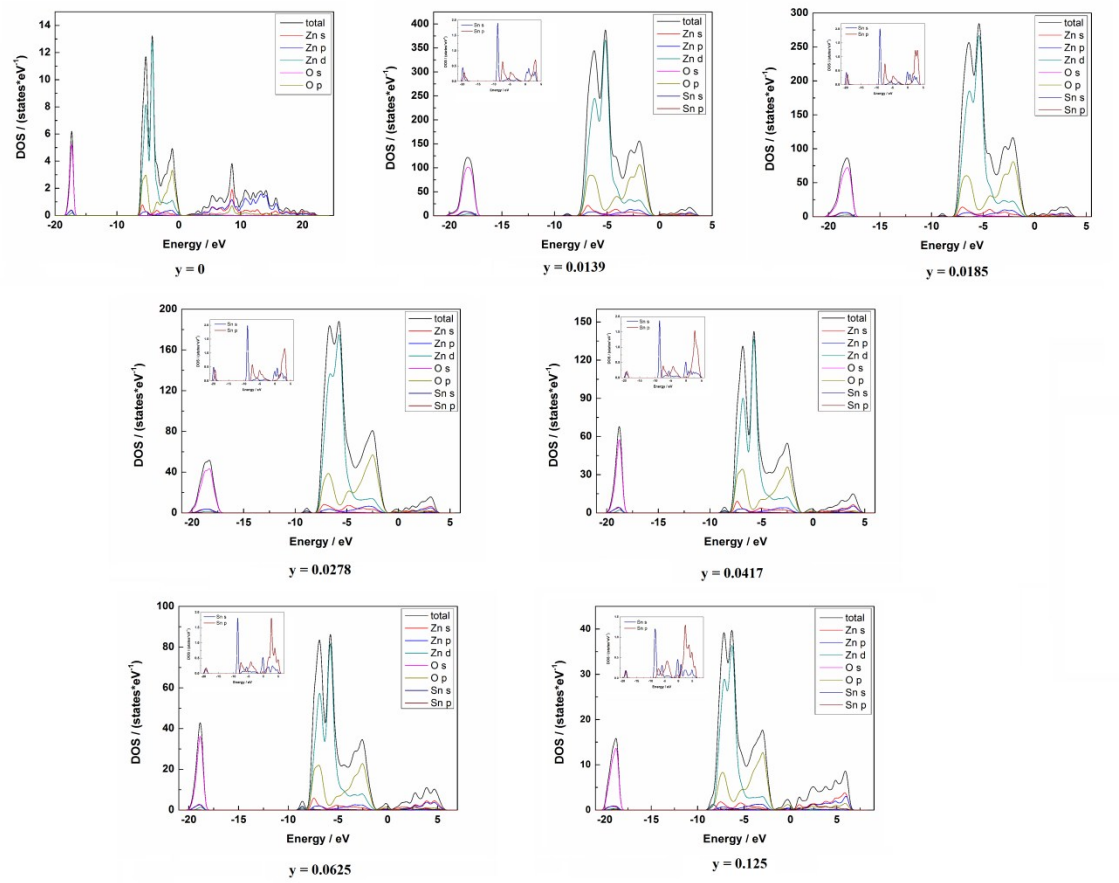

Figure s4 Calculated total DOS and partial DOS of $Zn_{1-y}Sn_yO$. (Small Figures on the upper left are PDOS of Sn^{4+})

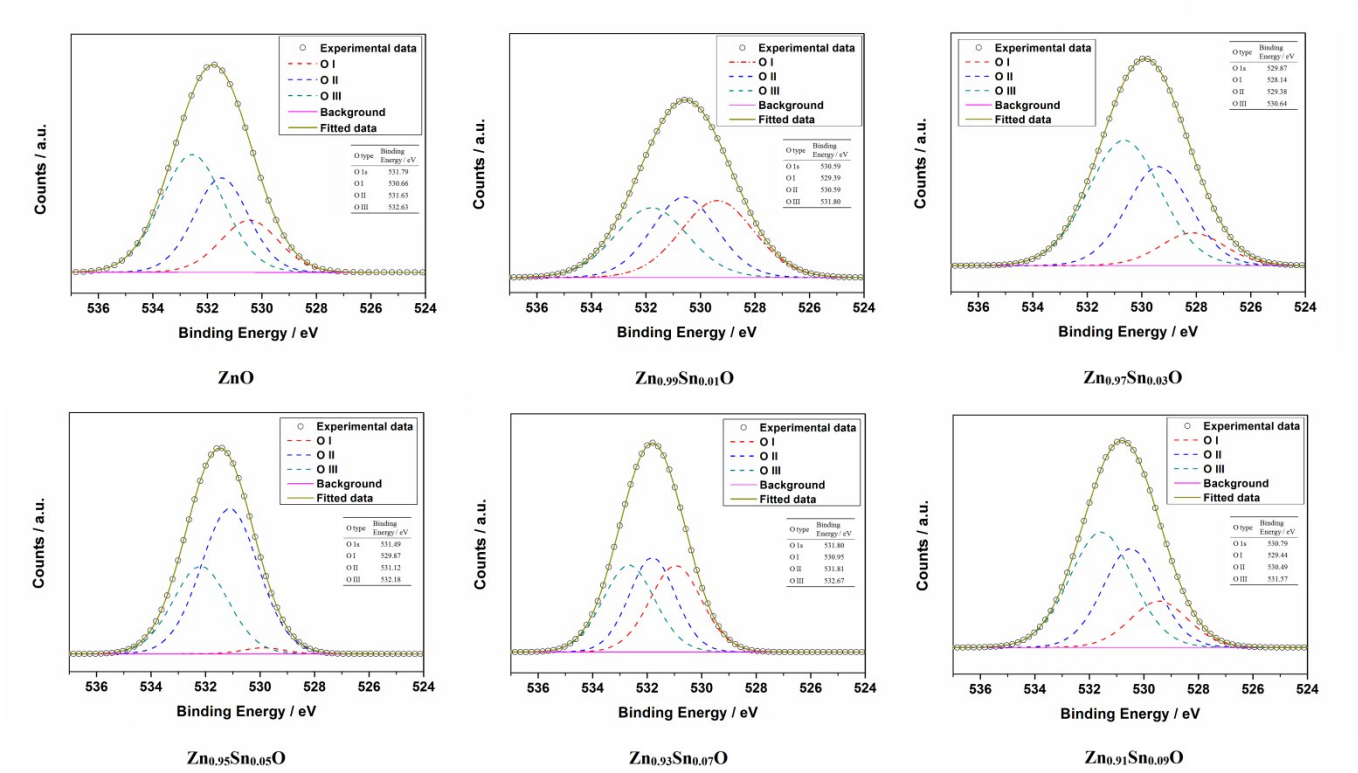

Figure s5 O 1s XPS spectra of $Zn_{1-y}Sn_yO$ QDs synthesized in 40 °C with 180 W ultrasonic power for 30 min.

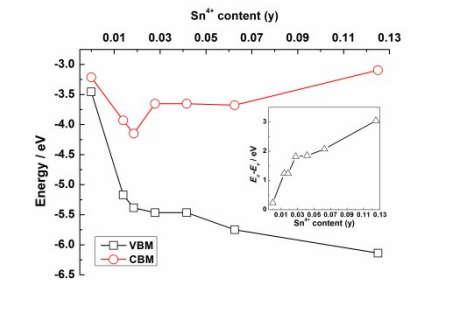

Figure s6 Orbital properties of Sn^{4+} doping ZnO.